



2020년 2월 14일(금), 15:45~17:30

Room J (하트 III, 6층)

**D. Thin Film Process Technology 분과**

**[FJ3-D] Memory Devices**

<p><b>FJ3-D-1</b> 15:45~16:15</p>	<p>[초청] <b>Three-Terminal Memristor</b> Hong-Sub Lee <i>Kangwon National University</i></p>
<p><b>FJ3-D-2</b> 16:15~16:45</p>	<p>[초청] <b>Atomic Layer Deposition of SrTiO<sub>3</sub> Thin Films for Dynamic Random Access Memory Capacitors</b> Woongkyu Lee <i>Department of Electrical Engineering, Myongji University</i></p>
<p><b>FJ3-D-3</b> 16:45~17:00</p>	<p><b>CVD NbSe<sub>2</sub> Buffer Layer to Control Active Metal Ions in Ag/NbSe<sub>2</sub>/HfO<sub>2</sub>/Pt Device for Stable Synaptic Functions</b> Yu-Rim Jeon<sup>1</sup>, Yonghun Kim<sup>2</sup>, and Changhwan Choi<sup>1</sup> <i><sup>1</sup>Division of Materials Science and Engineering, Hanyang University, <sup>2</sup>Surface Technology Division, KIMS</i></p>
<p><b>FJ3-D-4</b> 17:00~17:15</p>	<p><b>Synaptic and Nonvolatile Memory Characteristics in Ag/HfO<sub>2</sub>/Pt Structured Conductive Bridge Random Access Memory Devices</b> Haider Abbas and Changhwan Choi <i>Division of Materials Science and Engineering, Hanyang University</i></p>
<p><b>FJ3-D-5</b> 17:15~17:30</p>	<p><b>Mechanically Stretchable Charge-Trap Memory Transistors Fabricated on Ultra-Thin Polyimide Film with Wavy Dimensional Structures</b> Hyo-Eun Kim, Hye-Won Jang, and Sung-Min Yoon <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i></p>